SGM8261-1/SGM8261-2 High-Performance, Bipolar-Input, Ultra Low Noise Operational Amplifiers

GENERAL DESCRIPTION

The SGM8261-1 (single) and SGM8261-2 (dual) bipolar-input operational amplifiers achieve very low noise density with an ultra low distortion of 0.00002% at 1kHz. The SGM8261-1/2 offer rail-to-rail output swing to within 185mV of supply rails with a $2k\Omega$ load, which increases headroom and maximizes dynamic range. The devices also have a high output drive capability of ±65mA.

The devices operate over a wide supply range of 3.6V to 36V or $\pm 1.8V$ to $\pm 18V$, on only 3.8mA of supply current per amplifier. The SGM8261-1/2 operational amplifiers are unity-gain stable and provide excellent dynamic behavior over a wide range of load conditions.

The SGM8261-1 is available in a Green SOIC-8 package. The SGM8261-2 is available in Green SOIC-8, MSOP-8 and TDFN-3×3-8BL packages. They operate over an ambient temperature range of -40° C to $+85^{\circ}$ C.

FEATURES

- Superior Sound Quality
- Low Offset Voltage: ±350µV (MAX)
- Ultra Low Noise: $1.6nV/\sqrt{Hz}$ at 1kHz
- Ultra Low Distortion: 0.00002% at 1kHz
- High Slew Rate: 16V/µs
- Gain-Bandwidth Product: 16MHz (G = +1)
- High Open-Loop Gain: 140dB
- Unity-Gain Stable
- Low Quiescent Current: 3.8mA/Amplifier
- Rail-to-Rail Output
- Support Single or Dual Power Supplies: 3.6V to 36V or ±1.8V to ±18V
- -40°C to +85°C Operating Temperature Range
- Small Packaging: SGM8261-1 Available in a Green SOIC-8 Package SGM8261-2 Available in Green SOIC-8, MSOP-8 and TDFN-3×3-8BL Packages

APPLICATIONS

Professional Audio Equipment Analog and Digital Mixing Consoles High-End A/V Receivers

PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM8261-1	SOIC-8	-40°C to +85°C	SGM8261-1YS8G/TR	SGM 82611YS8 XXXXX	Tape and Reel, 2500
	SOIC-8	-40°C to +85°C	SGM8261-2YS8G/TR	SGM 82612YS8 XXXXX	Tape and Reel, 2500
SGM8261-2	MSOP-8	-40°C to +85°C	SGM8261-2YMS8G/TR	SGM82612 YMS8 XXXXX	Tape and Reel, 4000
	TDFN-3×3-8BL	-40°C to +85°C	SGM8261-2YTDD8G/TR	SGM 82612DD XXXXX	Tape and Reel, 4000

MARKING INFORMATION

NOTE: XXXXX = Date Code and Vendor Code.

XXXXX Vendor Code

- Date Code - Week Date Code - Year

Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, +V _S to -V _S	40V
Input Voltage Range (-V _S) - 0.3V to (+	+V _s) + 0.3V
Input Current (All pins except power supply pins).	±10mA
Output Short-Circuit Current	±100mA
Junction Temperature	+150°C
Storage Temperature Range65°C	to +150°C
Lead Temperature (Soldering, 10s)	+260°C
ESD Susceptibility	
НВМ	8000V
MM	300V
CDM	1000V

RECOMMENDED OPERATING CONDITIONS

Operating Temperature Range-40°C to +85°C

OVERSTRESS CAUTION

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

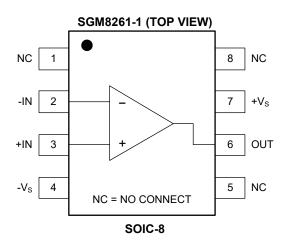
ESD SENSITIVITY CAUTION

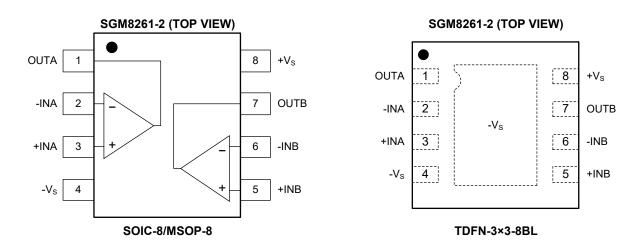
This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

PIN CONFIGURATIONS





NOTE:

For the TDFN-3×3-8BL package, connect thermal die pad to -V_S. Soldering the thermal pad improves heat dissipation and provides specified performance.

ELECTRICAL CHARACTERISTICS

(At $T_A = +25^{\circ}C$, $V_S = 4.5V$ to 36V or $V_S = \pm 2.25V$ to $\pm 18V$, $R_L = 2k\Omega$, $V_{CM} = V_{OUT} = V_S/2$, unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
Input Characteristics						
	V _S = ±15V		±100	±350		
Input Offset Voltage (Vos)	-40°C ≤ T _A ≤ +85°C			±450	μV	
Input Offset Voltage Drift (ΔV _{os} /ΔT)	V _S = ±15V		1		µV/°C	
	$V_{CM} = V_{OUT} = V_S/2$		±40	±300		
Input Bias Current (I _B)	-40°C ≤ T _A ≤ +85°C			±550	nA	
Input Offset Current (I _{os})	$V_{CM} = V_{OUT} = V_S/2$		±25	±165	nA	
Input Common Mode Voltage Range (V _{CM})		(-V _s) + 1.8		(+V _S) - 1.8	V	
	$V_{\rm S}$ = 4.5V, (-V _S) + 1.8V \leq V _{CM} \leq (+V _S) - 1.8V	102	120			
	$-40^{\circ}C \leq T_{A} \leq +85^{\circ}C$	99				
Common Mode Rejection Ratio (CMRR)	$V_{\rm S}$ = 36V, (-V _S) + 1.8V ≤ $V_{\rm CM}$ ≤ (+V _S) - 1.8V	122	135		dB	
out Bias Current (I _B) out Offset Current (I _{OS}) out Common Mode Voltage Range (V _{CM}) ommon Mode Rejection Ratio (CMRR) open-Loop Voltage Gain (A _{OL}) out Impedance ferential ommon Mode utput Characteristics atput Voltage Swing from Rail ttput Short-Circuit Current (I _{SC}) odio Performance tal Harmonic Distortion + Noise (THD+N) ermodulation Distortion (IMD)	$-40^{\circ}C \leq T_{A} \leq +85^{\circ}C$	110				
but CharacteristicsV_S = ±15Vut Offset Voltage Drift ($\Delta V_{OS}/\Delta T$)V_S = ±15VUt Offset Voltage Drift ($\Delta V_{OS}/\Delta T$)V_S = ±15Vut Bias Current (I_B)V_CM = V_{OUT} =ut Offset Current (I_{OS})V_CM = V_{OUT} =ut Offset Current (I_{OS})V_CM = V_{OUT} =ut Common Mode Voltage Range (V_CM)mmon Mode Rejection Ratio (CMRR)V_S = 4.5V, (-40°C < T_A <						

NOTE: 1. Full Power Bandwidth = SR/($2\pi \times V_P$), where SR = Slew Rate.

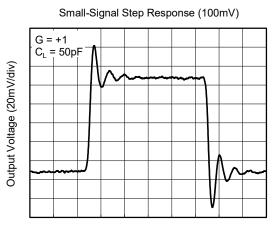
ELECTRICAL CHARACTERISTICS (continued)

(At $T_A = +25^{\circ}$ C, $V_S = 4.5$ V to 36V or $V_S = \pm 2.25$ V to ± 18 V, $R_L = 2k\Omega$, $V_{CM} = V_{OUT} = V_S/2$, unless otherwise noted.)

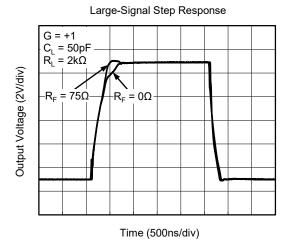
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
Noise Performance						
Input Voltage Noise	f = 20Hz to 20kHz		1.7		μV _{P-P}	
	f = 10Hz		5			
Input Voltage Noise Density (e _n)	f = 100Hz		2		nV/ _{√Hz}	
put Current Noise Density (in)	f = 1kHz		1.6			
Input Current Noise Density (in)	f = 1kHz		6		pA/√ _{Hz}	
Power Supply		·				
Supply Voltage (V _S)		±1.8		±18	V	
Specified Voltage (V _s)		±2.25		±18	V	
	V _S = 3.6V to 36V, I _{OUT} = 0		3.8	5		
	$-40^{\circ}C \leq T_{A} \leq +85^{\circ}C$			5.5	mA	
oise Performance aput Voltage Noise f aput Voltage Noise Density (e_n) f aput Current Noise Density (i_n) f ower Supply g upply Voltage (V_S) g pecified Voltage (V_S) g uiescent Current/Amplifier (I_Q) V ower Supply Rejection Ratio (PSRR) V	V _s = ±1.8V to ±18V		0.1	1		
	$-40^{\circ}C \leq T_{A} \leq +85^{\circ}C$			1.5	μV/V	

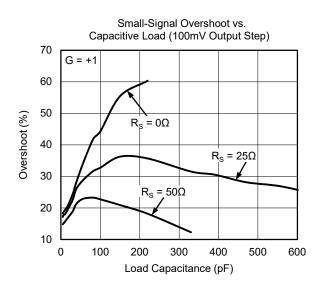
TYPICAL PERFORMANCE CHARACTERISTICS

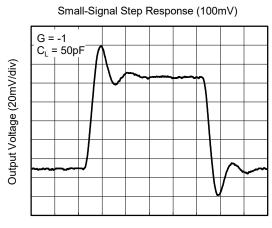
At $T_A = +25^{\circ}$ C, $V_S = \pm 15$ V and $R_L = 2k\Omega$, unless otherwise noted.



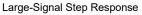
Time (100ns/div)

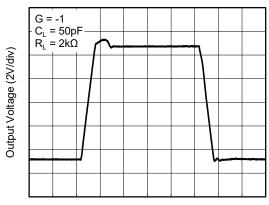




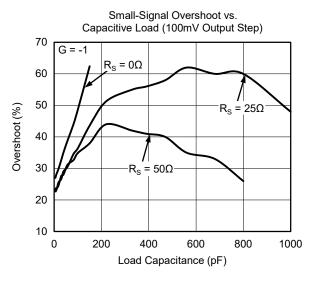


Time (100ns/div)



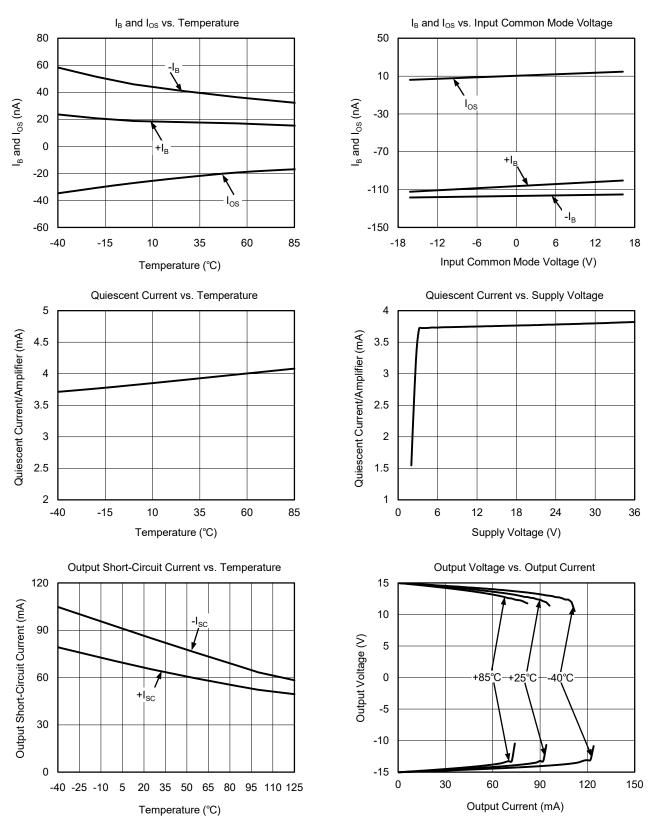






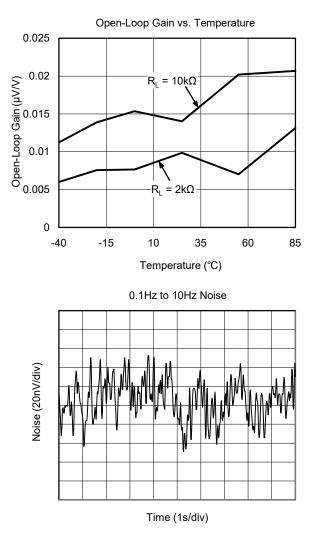
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

At $T_A = +25^{\circ}C$, $V_S = \pm 15V$ and $R_L = 2k\Omega$, unless otherwise noted.

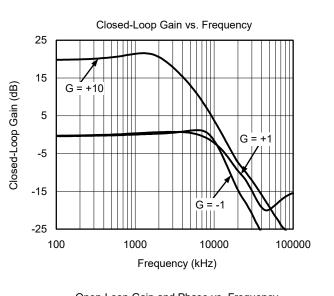


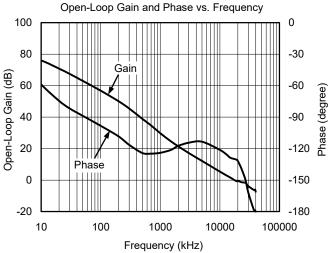
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

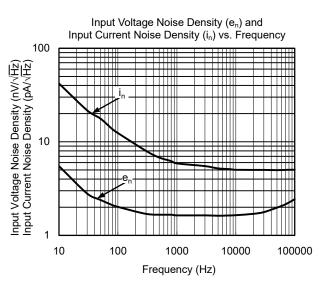
At $T_A = +25^{\circ}C$, $V_S = \pm 15V$ and $R_L = 2k\Omega$, unless otherwise noted.



Input Voltage Noise Density vs. Source Resistance 10000 Input Voltage Noise Density (nV/√Hz) Total Output 1000 . Voltage Noise 100 10 **Resistor Noise** 1 100 1000 10000 100000 1000000 Source Resistance (Ω)







= 600Ω

1000

R_{source}

1000

 $R_{source} = 150\Omega$

10000

100000

100000

100

600Ω

R

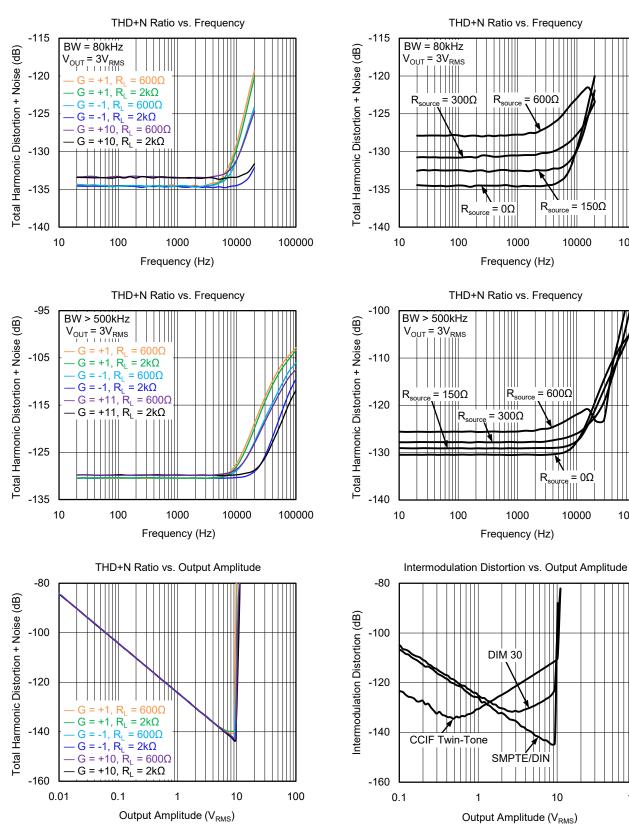
= 00

10000

10

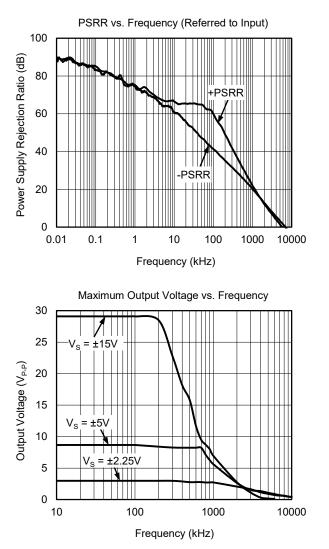
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

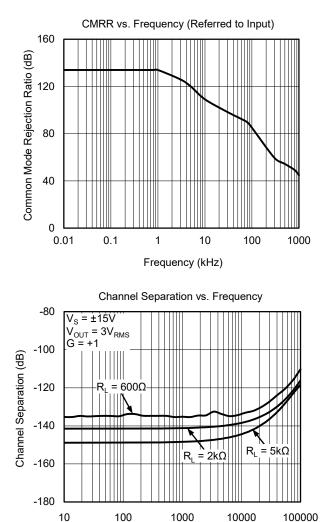
At $T_A = +25^{\circ}C$, $V_S = \pm 15V$ and $R_L = 2k\Omega$, unless otherwise noted.



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

At $T_A = +25^{\circ}C$, $V_S = \pm 15V$ and $R_L = 2k\Omega$, unless otherwise noted.





Frequency (Hz)

APPLICATION INFORMATION

The SGM8261-1/2 are unity-gain stable, precision operational amplifiers with very low noise; the devices are also free from output phase reversal. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device power supply pins. In most cases, 0.1μ F capacitors are adequate.

Operating Voltage

The SGM8261-1/2 operational amplifiers operate from 4.5V to 36V or ±2.25V to ±18V supplies while maintaining excellent performance. However, some applications do not require equal positive and negative output voltage swing. With the SGM8261-1/2, power supply voltages do not need to be equal. For example, the positive supply could be set to 25V with the negative supply at -5V. In all cases, the input common mode voltage must be maintained within the specified range. In addition, key parameters are assured over the specified temperature range of $T_A = -40^{\circ}$ C to +85°C.

Input Protection

The input terminals of the SGM8261-1/2 are protected from excessive differential voltage with back-to-back diodes, as Figure 1 illustrates. In most circuit applications, the input protection circuitry has no consequence. However, in low-gain or G = +1 circuits, fast ramping input signals can forward bias these diodes because the output of the amplifier cannot respond rapidly enough to the input ramp. If the input signal is fast enough to create this forward bias condition, the input signal current must be limited to 10mA or less. If the input signal current is not inherently limited, an input series resistor (R_I) and/or a feedback resistor (R_F) can be used to limit the signal input current. This input series resistor degrades the low-noise performance of the SGM8261-1/2 and is examined in the following Noise Performance section. Figure 1 shows an example configuration when both current-limit input and feedback resistors are used.

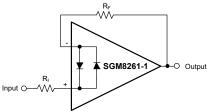


Figure 1. Input Current Limit

Noise Performance

Equation 1 shows the total circuit noise for varying source impedances with the operational amplifier in a unity-gain configuration (Figure 2, no feedback resistor network, and therefore no additional noise contributions).

The SGM8261-1/2 (GBP = 16MHz, G = +1) is shown with total circuit noise calculated. The operational amplifier itself contributes both a voltage noise component and a current noise component. The voltage noise is commonly modeled as a time-varying component of the offset voltage. The current noise is modeled as the time-varying component of the input bias current and reacts with the source resistance to create a voltage component of noise. Therefore, the lowest noise operational amplifier for a given application depends on the source impedance. For low source impedance, current noise is negligible, and voltage noise generally dominates. The low voltage noise of the SGM8261-1/2 operational amplifiers makes them good choices for use in applications where the source impedance is less than 1kΩ.

The following equation shows the calculation of the total circuit noise:

$$E_{o}^{2} = e_{n}^{2} + (i_{n}R_{s})^{2} + 4kTR_{s}$$
 (1)

Where e_n = voltage noise, i_n = current noise, R_s = source impedance, k = Boltzmann's constant = 1.38 × 10⁻²³ J/K, T = temperature in degrees Kelvin (K).

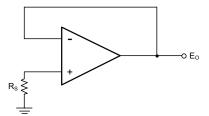


Figure 2. Unity-Gain Buffer Configuration

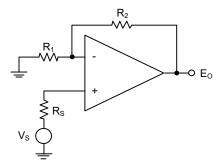
APPLICATION INFORMATION (continued)

Basic Noise Calculations

Design of low-noise operational amplifier circuits requires careful consideration of a variety of possible noise contributors: noise from the signal source, noise generated in the operational amplifier and noise from the feedback network resistors. The total noise of the circuit is the root-sum-square combination of all noise components.

The resistive portion of the source impedance produces thermal noise proportional to the square root of the resistance. The source impedance is usually fixed; consequently, select the operational amplifier and the

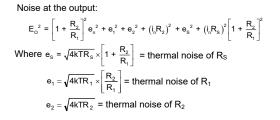
Noise in Non-Inverting Gain Configuration



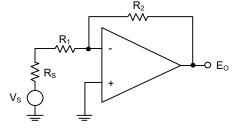
feedback resistors to minimize the respective contributions to the total noise.

Figure 3 illustrates both inverting and non-inverting operational amplifier circuit configurations with gain. In circuit configurations with gain, the feedback network resistors also contribute noise.

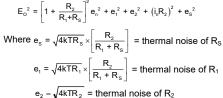
The current noise of the operational amplifier reacts with the feedback resistors to create additional noise components. The feedback resistor values can generally be chosen to make these noise sources negligible. The equations for total noise are shown for both configurations.



Noise in Inverting Gain Configuration







NOTE: For the SGM8261-1/2 operational amplifier at 1kHz, $e_n = 1.6nV/\sqrt{Hz}$ and $i_n = 6pA/\sqrt{Hz}$.

Figure 3. Noise Calculation in Gain Configurations

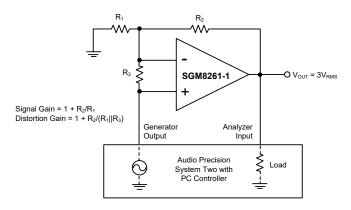
APPLICATION INFORMATION (continued)

Total Harmonic Distortion Measurements

The SGM8261-1/2 operational amplifiers have excellent distortion characteristics. THD + noise is below 0.00015% (G = +1, V_{OUT} = $3V_{RMS}$, BW = 80kHz) throughout the audio frequency range, 20Hz to 20kHz, with a 2k Ω load.

The distortion produced by SGM8261-1/2 operational amplifiers is below the measurement limit of many commercially available distortion analyzers. However, a special test circuit (such as Figure 4 shows) can be used to extend the measurement capabilities.

Operational amplifier distortion can be considered an internal error source that can be referred to the input. Figure 4 shows a circuit that causes the operational amplifier distortion to be 101 times (or approximately 40dB) greater than that normally produced by the operational amplifier. The addition of R_3 to the otherwise standard non-inverting amplifier configuration alters the feedback factor or noise gain of the circuit. The closed-loop gain is unchanged, but the feedback available for error correction is reduced by a factor of 101, thus extending the resolution by 101. Note that the input signal and load applied to the operational amplifier are the same as with conventional feedback without R_3 . The value of R_3 should be kept small to minimize its effect on the distortion measurements.



SIG. Gain	DIST. Gain	R ₁	R ₂	R ₃
1	101	∞	1kΩ	10Ω
-1	101	4.99kΩ	4.99kΩ	49.9Ω
+10	110	549Ω	4.99kΩ	49.9Ω

Figure 4. Distortion Test Circuit

Validity of this technique can be verified by duplicating measurements at high gain and/or high frequency where the distortion is within the measurement capability of the test equipment. Measurements for this datasheet were made with an Audio Precision System Two distortion/noise analyzer, which greatly simplifies such repetitive measurements. The measurement technique can, however, be performed with manual distortion measurement instruments.

Capacitive Loads

The dynamic characteristics of the SGM8261-1/2 have been optimized for commonly encountered gains, loads, and operating conditions. The combination of low closed-loop gain and high capacitive loads decreases the phase margin of the amplifier and can lead to gain peaking or oscillations. As a result, heavier capacitive loads must be isolated from the output. The simplest way to achieve this isolation is to add a small resistor (R_s equal to 50 Ω , for example) in series with the output.

Power Dissipation

SGM8261-1/2 operational amplifiers are capable of driving $2k\Omega$ loads with a power supply voltage up to ±18V. Internal power dissipation increases when operating at high supply voltages. Copper leadframe construction used in the SGM8261-1/2 operational amplifiers improves heat dissipation compared to conventional materials. Circuit board layout can also help minimize junction temperature rise. Wide copper traces help dissipate the heat by acting as an additional heat sink. Temperature rise can be further minimized by soldering the devices to the circuit board rather than using a socket.

Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions has electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

APPLICATION CIRCUIT

Figure 5 shows how to use the SGM8261-1/2 as an amplifier for professional audio headphones. The circuit

shows the left side stereo channel. An identical circuit is used to drive the right side stereo channel.

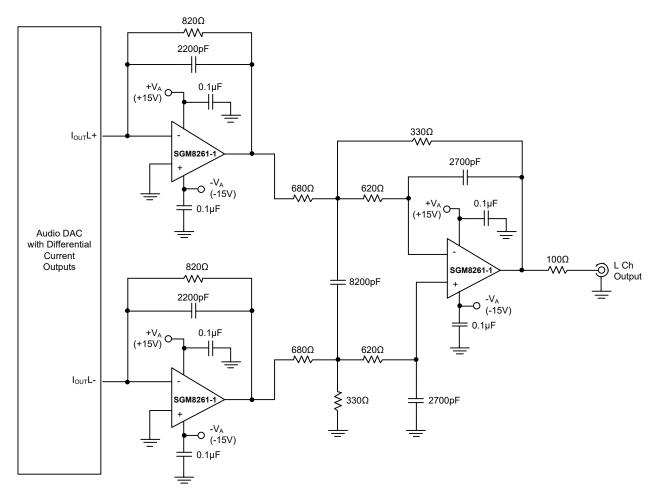


Figure 5. Audio DAC Post Filter (I/V Converter and Low-Pass Filter)

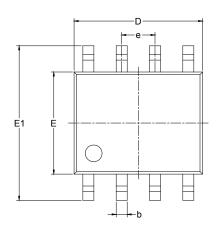
REVISION HISTORY

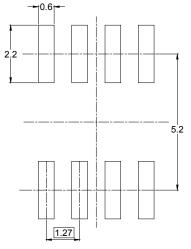
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

APRIL 2020 – REV.A.1 to REV.A.2	Page
Deleted TDFN-3×3-8AL Package	All
Updated Typical Performance Characteristics section	
MAY 2017 – REV.A to REV.A.1	Page
Changed supply voltage range	1
Changes from Original (MAY 2017) to REV.A	Page
Changed from product preview to production data	

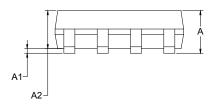
PACKAGE OUTLINE DIMENSIONS

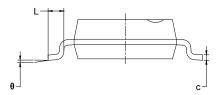
SOIC-8





RECOMMENDED LAND PATTERN (Unit: mm)

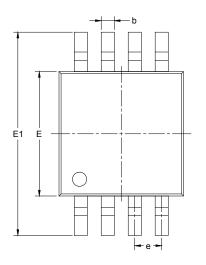


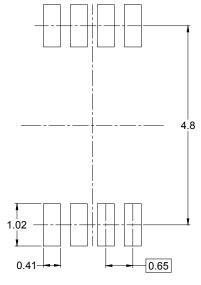


Symbol		nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.27 BSC		0.050	BSC	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

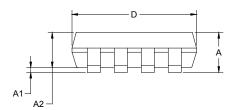
PACKAGE OUTLINE DIMENSIONS

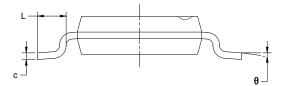
MSOP-8





RECOMMENDED LAND PATTERN (Unit: mm)

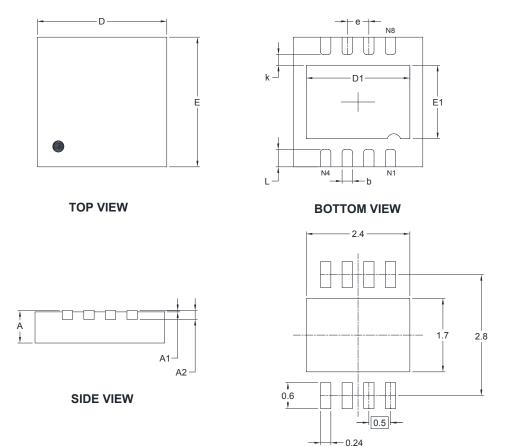




Symbol		nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
A	0.820	1.100 0.032		0.043	
A1	0.020	0.150	0.001	0.006	
A2	0.750	0.950	0.030	0.037	
b	0.250	0.380	0.010	0.015	
С	0.090	0.230	0.004	0.009	
D	2.900	3.100	0.114	0.122	
E	2.900	3.100	0.114	0.122	
E1	4.750	5.050	0.187	0.199	
е	0.650	BSC	0.026	BSC	
L	0.400	0.800	0.016	0.031	
θ	0°	6°	0°	6°	

PACKAGE OUTLINE DIMENSIONS

TDFN-3×3-8BL

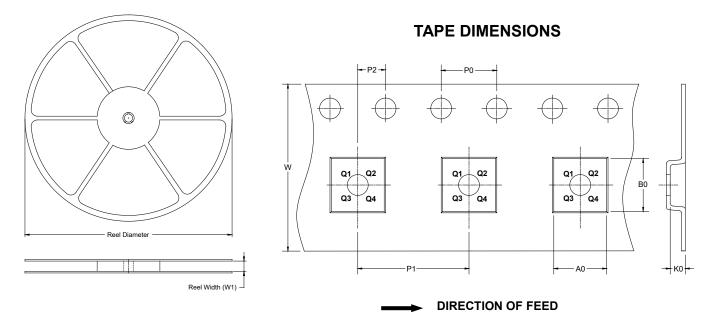


RECOMMENDED LAND PATTERN (Unit: mm)

Symbol	-	nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
A	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A2	0.203	B REF	0.008 REF		
D	2.900	3.100	0.114	0.122	
D1	2.300	2.500	0.091	0.098	
E	2.900	3.100	0.114	0.122	
E1	1.600	1.800	0.063	0.071	
k	0.200	0.200 MIN		3 MIN	
b	0.180	0.300	0.007	0.012	
e	0.500 TYP		0.020) TYP	
L	0.300	0.500	0.012	0.020	

TAPE AND REEL INFORMATION

REEL DIMENSIONS

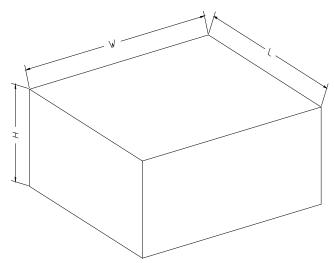


NOTE: The picture is only for reference. Please make the object as the standard.

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
SOIC-8	13″	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1
MSOP-8	13″	12.4	5.20	3.30	1.50	4.0	8.0	2.0	12.0	Q1
TDFN-3×3-8BL	13″	12.4	3.35	3.35	1.13	4.0	8.0	2.0	12.0	Q1

KEY PARAMETER LIST OF TAPE AND REEL

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton	
13″	386	280	370	5	DD0002